ABSTRACT

A method for producing a semiconductor device includes attaching a film B of a dicing/die-bonding integrated film, the integrated film including a dicing film (film A) having a base film and a pressure-sensitive adhesive layer provided on the base film, and a die-bonding film (film B) provided on the pressure-sensitive adhesive layer, to a plurality of semiconductor chips obtained by singulating a semiconductor wafer, under a heating condition; and singulating the film B by expanding the film A under a cooling condition, thereby producing a semiconductor chip with film B piece, which includes the semiconductor chip and a film B piece obtained by singulating the film B. The thickness of the film B is 20 μm or less. The tensile stress of the film A at 20% elongation at 0°C in a tensile test is 15 MPa or more. The thermal shrinkage rate at 70°C in thermomechanical analysis is 5% or less.

No Suitable Figure.